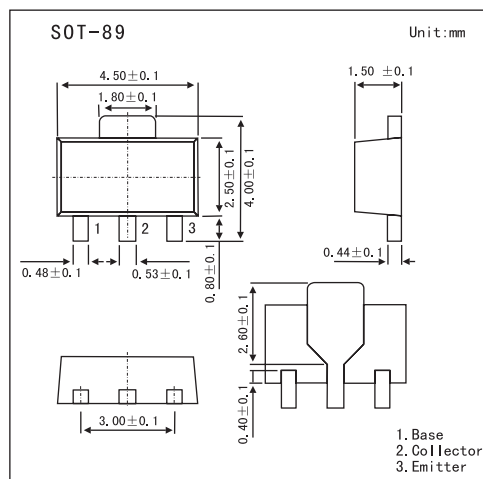


2SD1280

■ Features

- Low collector-emitter saturation voltage $V_{CE(sat)}$.
- Satisfactory operation performances at high efficiency with the lowvoltage power supply.



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	20	V
Collector-emitter voltage	V_{CEO}	20	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	1	A
Peak collector current	I_{CP}	2	A
Collector power dissipation	P_C	1	W
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-emitter voltage	V_{CEO}	$I_C = 1\text{ mA}, I_B = 0$	20			V
Emitter-base voltage	V_{EBO}	$I_E = 10\ \mu\text{A}, I_C = 0$	5			V
Collector-base cutoff current	I_{CBO}	$V_{CB} = 10\text{ V}, I_B = 0$			1	μA
Forward current transfer ratio	h_{FE}	$V_{CE} = 2\text{ V}, I_C = 0.5\text{ A}$	90		280	
		$V_{CE} = 2\text{ V}, I_C = 1.5\text{ A}$	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 1\text{ A}, I_B = 50\text{ mA}$			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = 500\text{ mA}, I_B = 50\text{ mA}$			1.2	V
Transition frequency	f_T	$V_{CB} = 6\text{ V}, I_E = -50\text{ mA}, f = 200\text{ MHz}$		150		MHz
Collector output capacitance	C_{ob}	$V_{CB} = 6\text{ V}, I_E = 0, f = 1\text{ MHz}$		18		pF

■ h_{FE} Classification

Marking	R		
Rank	Q	R	S
h_{FE}	90~155	130~210	180~280